## **AMENDMENTS TO THE SPECIFICATION:**

Please amend the specification by inserting before the first line, the sentence:

This is a divisional application of Serial No. 10/329,680, filed December 27, 2002.

Amend the first paragraph at page 3 as follows:

A source/drain region 17 is formed by implanting N-type impurity ions using the dummy gate 15 16 as a mask, and then performing a drive-in process thereon.